DISCRETE SEMICONDUCTORS

DATA SHEET

BTA216X series B Three quadrant triacs high commutation

Product specification

September 2019



WeEn Semiconductors Product specification

Three quadrant triacs high commutation

BTA216X series B

GENERAL DESCRIPTION

Planar passivated high commutation triacs in a full pack, plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

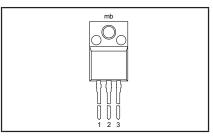
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} $I_{T(RMS)}$ I_{TSM}	BTA216X- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500B 500 16 140	600B 600 16 140	800B 800 16 140	V A A

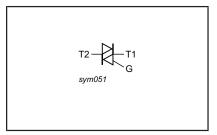
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	,	MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		16		Α
I _{TSM}	Non-repetitive peak on-state current	$T_{hs} \le 38 ^{\circ}C$ full sine wave; $T_{j} = 25 ^{\circ}C$ prior to surge					
		t = 20 ms t = 16.7 ms	-		140 150		A A
l²t dl _⊤ /dt	l ² t for fusing Repetitive rate of rise of on-state current after	t = 10.7 ms t = 10 ms l _{TM} = 20 A; l _G = 0.2 A; dl _G /dt = 0.2 A/µs	-		98 100		A ² s A/μs
$\begin{matrix} I_{GM} \\ V_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	triggering Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms	- - -		2 5 5 0.5		A V W
T_{stg}	Storage temperature Operating junction temperature	period	-40 -		150 125		Ç

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	-		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	ľ	full or half cycle with heatsink compound without heatsink compound	-	- -	4.0 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
·GI	and ingger content	T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
-		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	31	60	mA
V _T	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.5	V
$egin{array}{c} I_{H} \\ V_{T} \\ V_{GT} \end{array}$	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	0.25	0.4	<u>-</u> _	V
$ I_D $	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 °C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/μs
	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}$; $T_j = 125 ^{\circ}\text{C}$; $I_{T(RMS)} = 16 \text{ A}$; without snubber; gate open circuit	-	28	-	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

 $[\]boldsymbol{2}$ Device does not trigger in the T2-, G+ quadrant.

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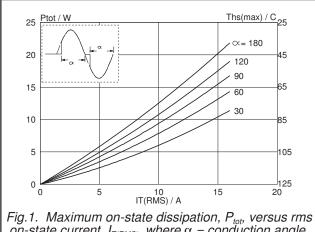


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

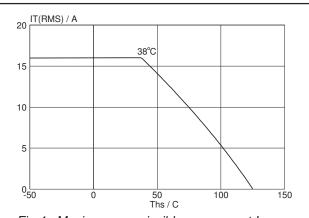


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

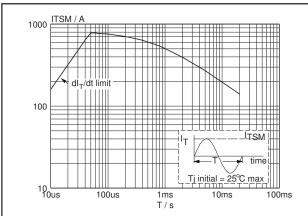


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

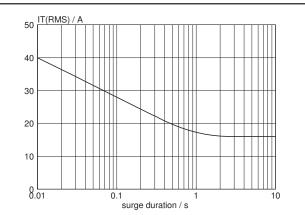


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38$ °C.

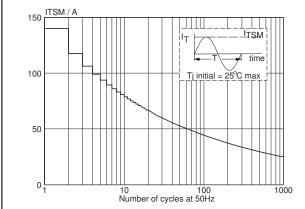


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

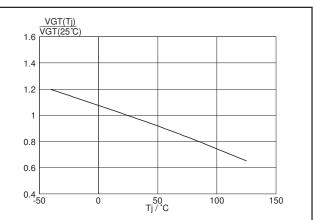
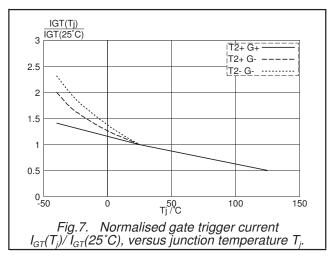


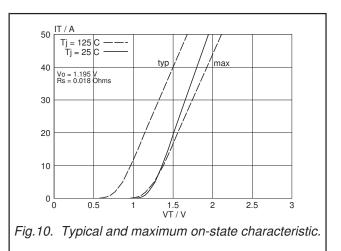
Fig.6. Normalised gate trigger voltage $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$, versus junction temperature T_i

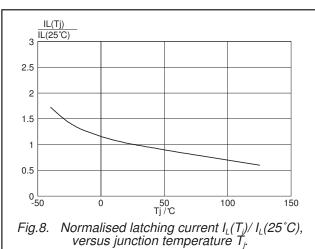
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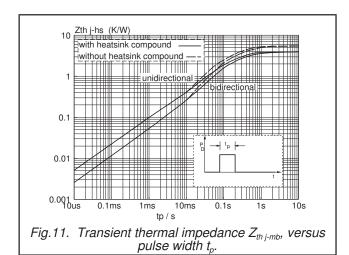
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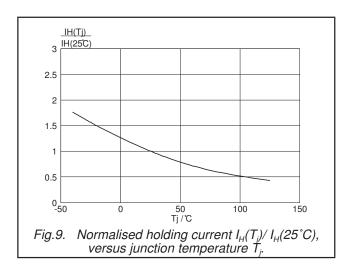
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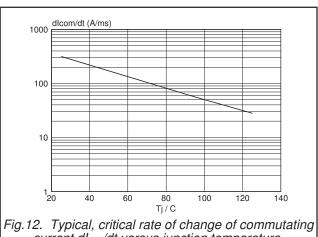










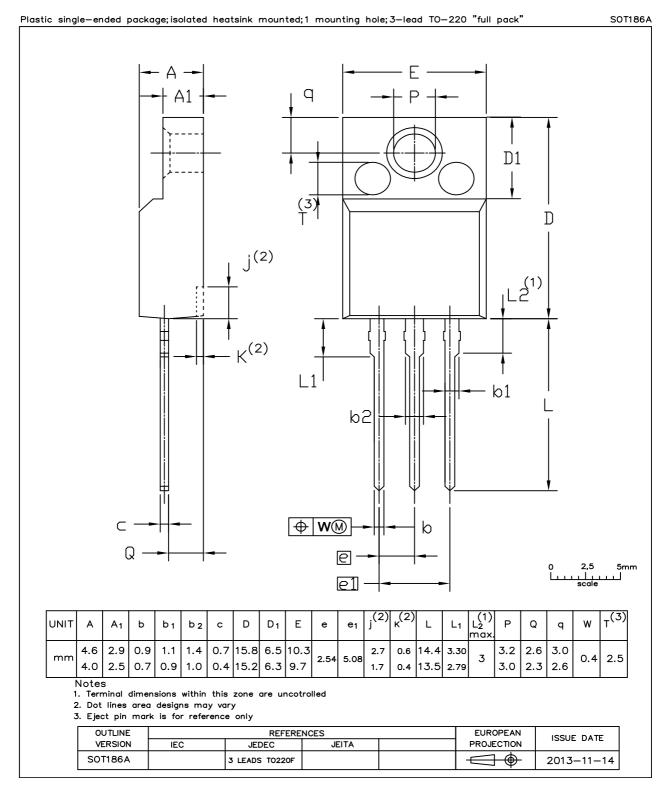


current dl_{com}/dt versus junction temperature.

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MECHANICAL DATA



Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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